

SANYO Semiconductors DATA SHEET

2SC4919-S-

NPN Epitaxial Planar Silicon Transistor Muting Circuit Applications

Features

- Ultrasmall-sized package permitting applied sets to be made small and slim.
- · Small output capacitance.
- · Low collector-to-emitter saturation voltage.
- Low ON resistance.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		25	V
Collector-to-Emitter Voltage	VCEO		15	V
Emitter-to-Base Voltage	VEBO		15	V
Collector Current	IC		100	mA
Collector Current (Pulse)	ICP		200	mA
Base Current	IB		20	mA
Collector Dissipation	PC		150	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			1.1
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =15V, I _E =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			0.1	μΑ
DC Current Gain	hFE	V _{CE} =2V, I _C =5mA	800		3200	
Gain-Bandwidth Product	fΤ	V _{CE} =5V, I _C =10mA		240		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		1.4		pF

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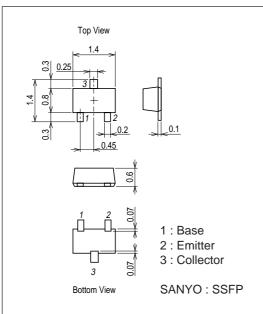
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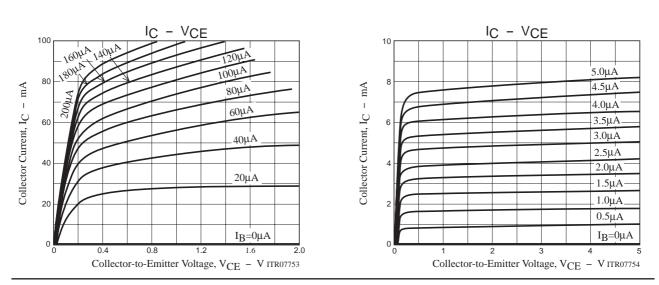
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=10mA, IB=1mA		14	30	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=10mA, IB=1mA		0.74	1.1	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10μA, I _E =0A	25			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	15			V
On Resistance	Ron	I _B =3mA, f=1MHz		0.9		Ω

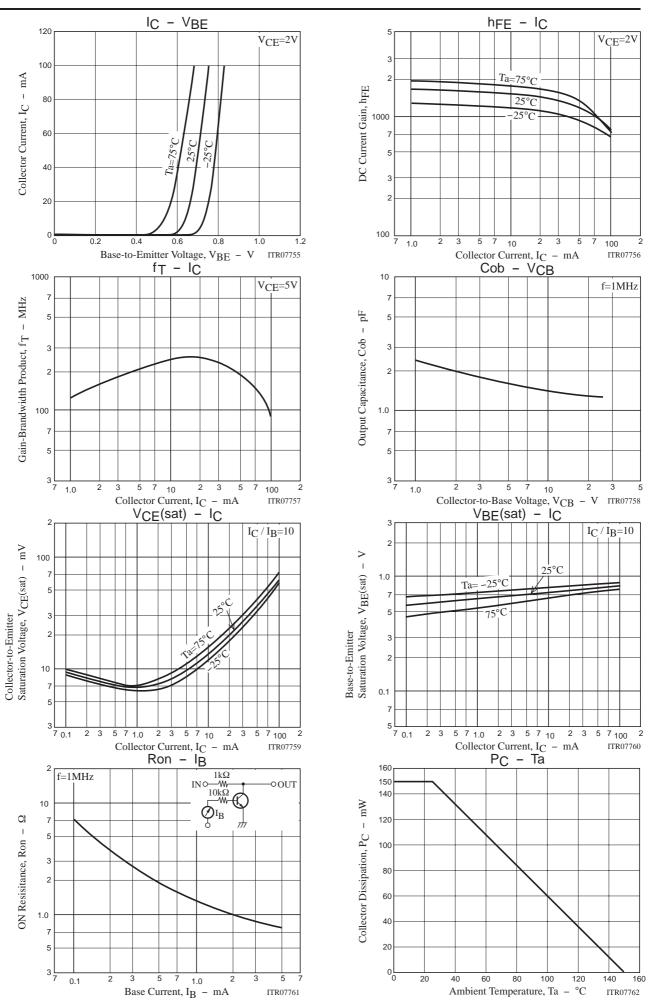
Package Dimensions

unit : mm (typ)

7029-002







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